



# P-Channel Enhancement-Mode Vertical DMOS FET

## Features

- ▶ Low threshold (-2.0V max.)
- ▶ High input impedance
- ▶ Low input capacitance
- ▶ Fast switching speeds
- ▶ Low on-resistance
- ▶ Free from secondary breakdown
- ▶ Low input and output leakage

## Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Battery operated systems
- ▶ Photo voltaic drives
- ▶ Analog switches
- ▶ General purpose line drivers
- ▶ Telecom switches

## Ordering Information

Part Number	Package Option	Packing
TP2640LG-G	8-Lead SOIC	2500/Reel
TP2640N3-G	3-Lead TO-92	1000/Bag
TP2640N3-G P002	3-Lead TO-92	2000/Reel
TP2640N3-G P003		
TP2640N3-G P005		
TP2640N3-G P013		
TP2640N3-G P014		

-G denotes a lead (Pb)-free / RoHS compliant package.  
 Contact factory for Wafer / Die availability.  
 Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

## Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	$BV_{DSS}$
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	$-55^{\circ}C$ to $+150^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

## Typical Thermal Resistance

Package	$\theta_{ja}$
8-Lead SOIC	$101^{\circ}C/W$
TO-92	$132^{\circ}C/W$

## General Description

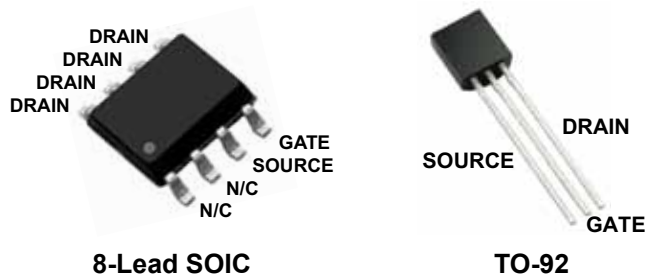
This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Product Summary

$BV_{DSS}/BV_{DGS}$	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	$V_{GS(th)}$ (max)
-400V	$15\Omega$	-2.0A	-0.7V

## Pin Configuration



## Product Marking



YY = Year Sealed  
 WW = Week Sealed  
 L = Lot Number  
 \_\_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or **8-Lead SOIC**



YY = Year Sealed  
 WW = Week Sealed  
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Package may or may not include the following marks: Si or **TO-92**

## Thermal Characteristics

Package	$I_D$ (continuous) <sup>†</sup>	$I_D$ (pulsed)	Power Dissipation @ $T_A = 25^\circ\text{C}$	$I_{DR}$ <sup>‡</sup>	$I_{DRM}$
8-Lead SOIC	-86mA	-600mA	0.74W <sup>‡</sup>	-86mA	-600mA
TO-92	-180mA	-0.8mA	1.0W	-180mA	-0.8mA

<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_J$ .

<sup>‡</sup> Mounted on FR5 board, 25mm x 25mm x 1.57mm.

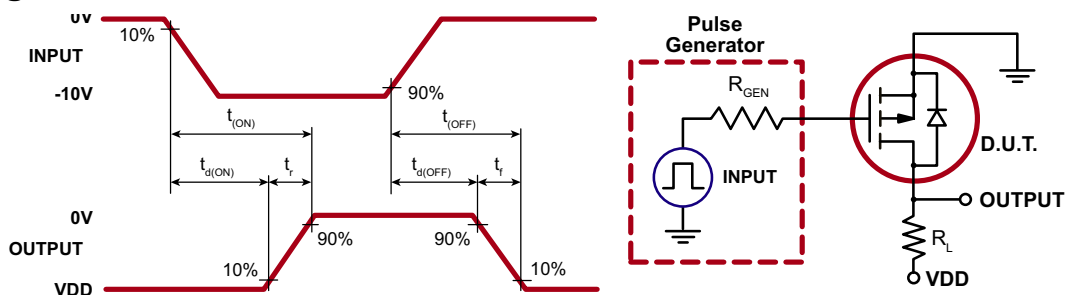
## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$BV_{DSS}$	Drain-to-source breakdown voltage	-400	-	-	V	$V_{GS} = 0V, I_D = -2.0mA$
$V_{GS(th)}$	Gate threshold voltage	-0.8	-	-2.0	V	$V_{GS} = V_{DS}, I_D = -1.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	5.0	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = -1.0mA$
$I_{GSS}$	Gate body leakage	-	-	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
$I_{DSS}$	Zero gate voltage drain current	-	-	-1.0	$\mu\text{A}$	$V_{GS} = 0V, V_{DS} = -100V$
				-10.0	$\mu\text{A}$	$V_{GS} = 0V, V_{DS} = \text{Max rating}$
				-1.0	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
$I_{D(ON)}$	On-state drain current	-0.7	-	-	A	$V_{GS} = -10V, V_{DS} = -25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	12	15	$\Omega$	$V_{GS} = -2.5V, I_D = -20mA$
			11	15		$V_{GS} = -4.5V, I_D = -150mA$
			11	15		$V_{GS} = -10V, I_D = -300mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	0.75	%/ $^\circ\text{C}$	$V_{GS} = -10V, I_D = -300mA$
$G_{FS}$	Forward transconductance	200	-	-	mmho	$V_{DS} = -25V, I_D = -300mA$
$C_{ISS}$	Input capacitance	-	-	300	pF	$V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz$
$C_{OSS}$	Common source output capacitance	-	-	50		
$C_{RSS}$	Reverse transfer capacitance	-	-	12		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	$V_{DD} = -25V, I_D = -300mA, R_{GEN} = 25\Omega$
$t_r$	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	60		
$t_f$	Fall time	-	-	40		
$V_{SD}$	Diode forward voltage drop	-	-	-1.8	V	$V_{GS} = 0V, I_{SD} = -200mA$
$t_{rr}$	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = -200mA$

**Notes:**

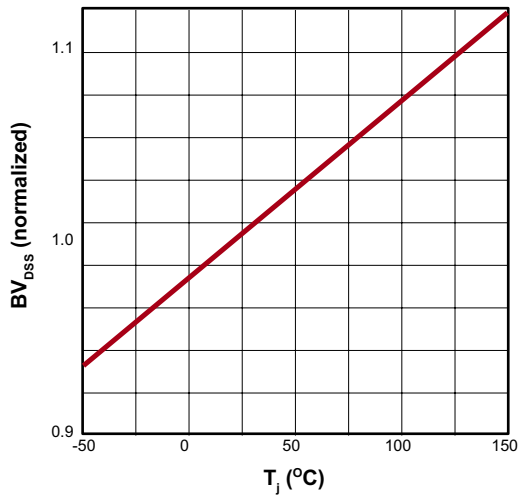
1. All D.C. parameters 100% tested at 25C unless otherwise stated. (Pulse test: 300s pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

## Switching Waveforms and Test Circuit

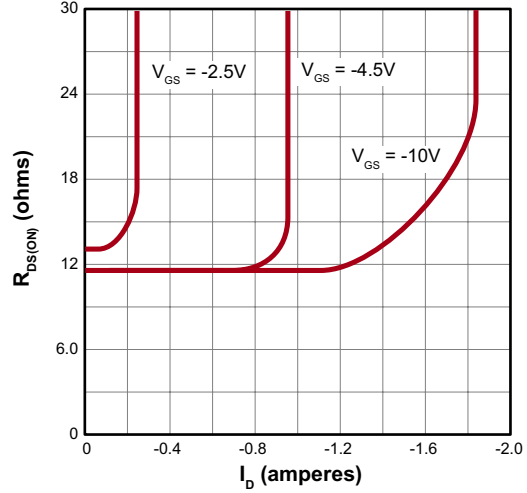


# Typical Performance Curves

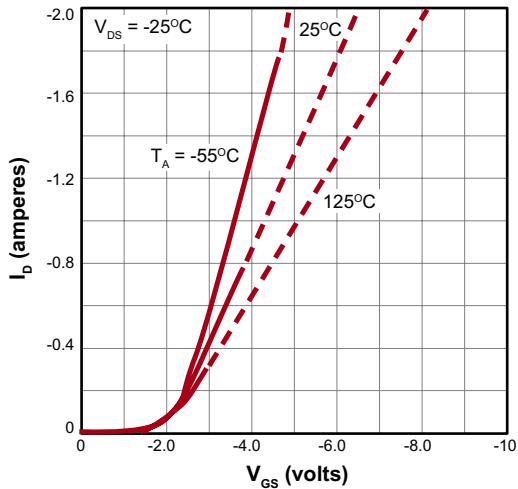
**BV<sub>DSS</sub> Variation with Temperature**



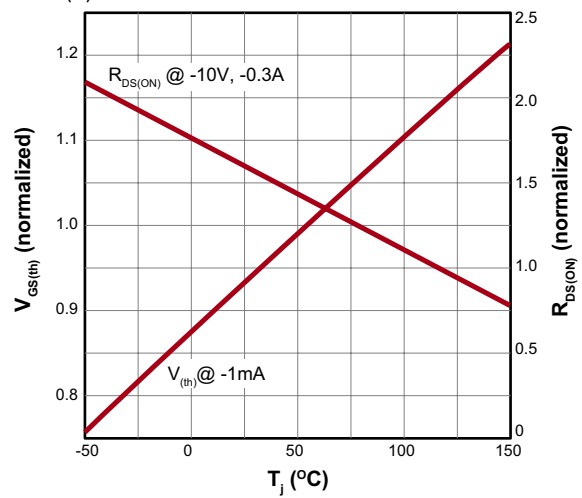
**On-Resistance vs. Drain Current**



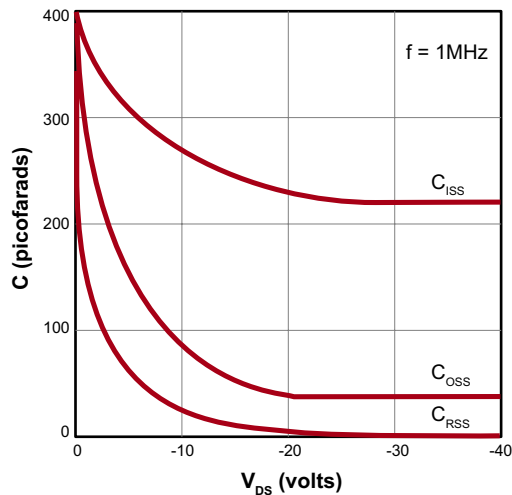
**Transfer Characteristics**



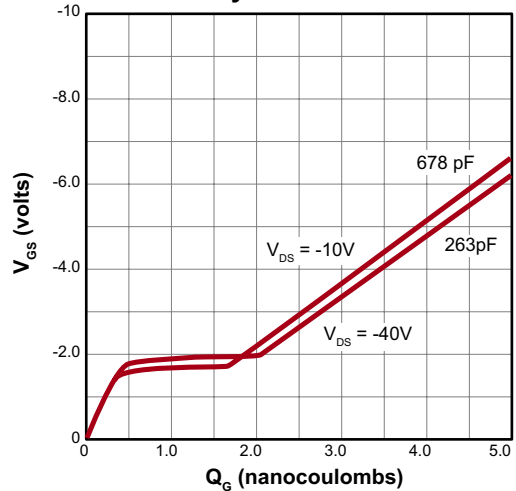
**V<sub>GS(th)</sub> and R<sub>DS</sub> Variation with Temperature**



**Capacitance vs. Drain-to-Source Voltage**

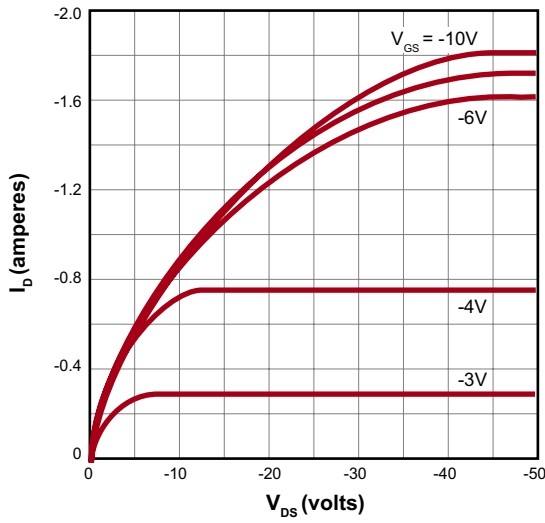


**Gate Drive Dynamic Characteristics**

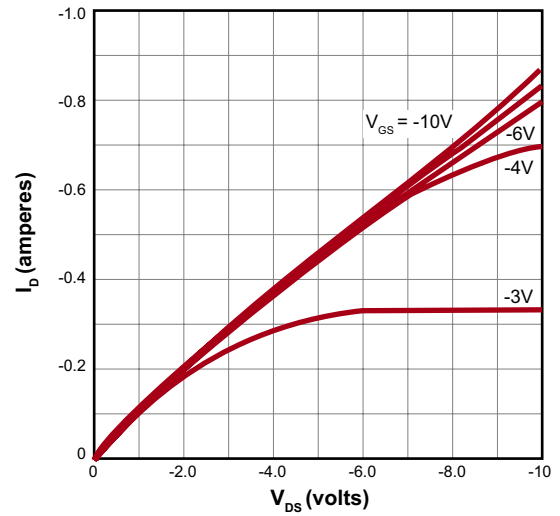


Typical Performance Curves (cont.)

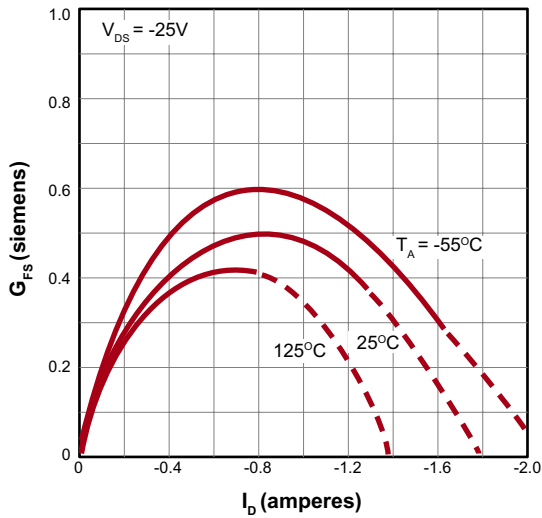
Output Characteristics



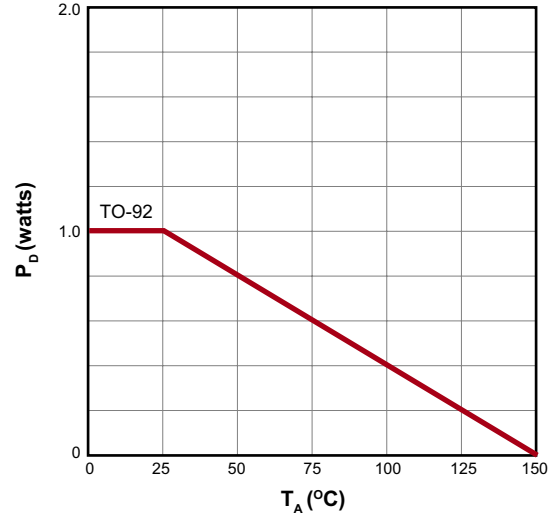
Saturation Characteristics



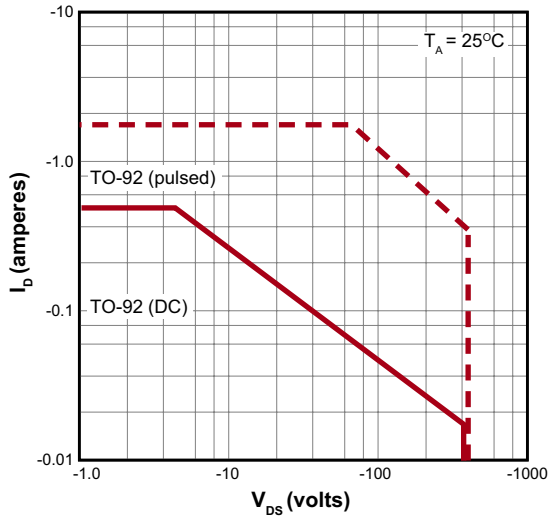
Transconductance vs. Drain Current



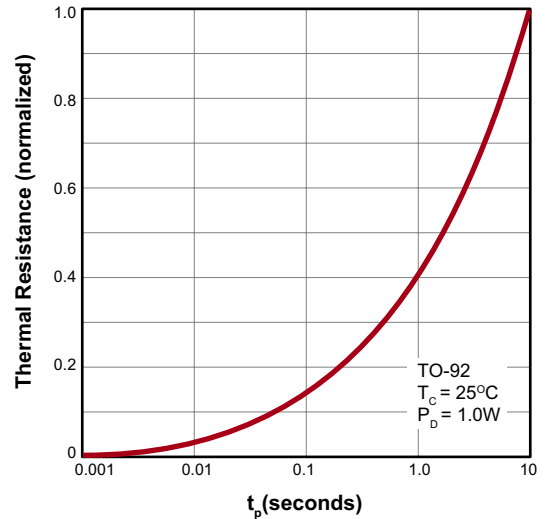
Power Dissipation vs. Temperature



Maximum Rated Safe Operating Area

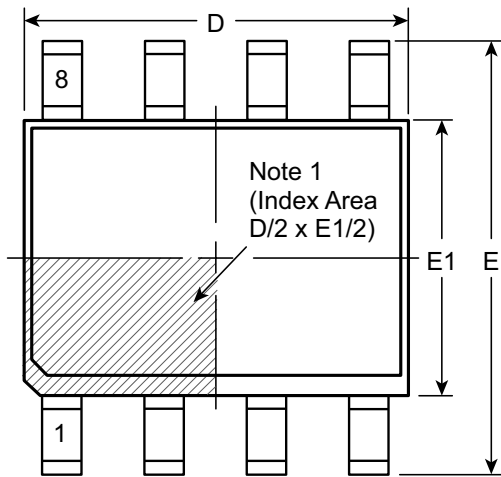


Thermal Response Characteristics

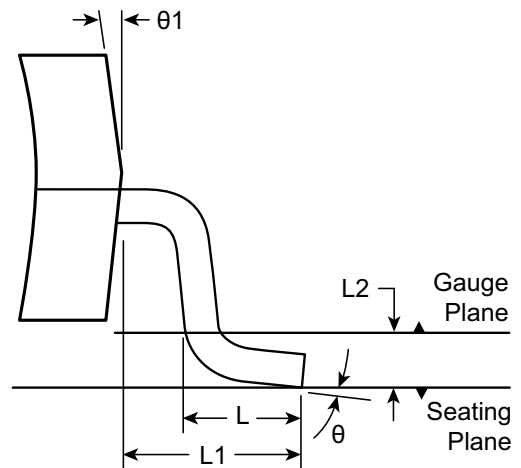


# 8-Lead SOIC (Narrow Body) Package Outline (LG)

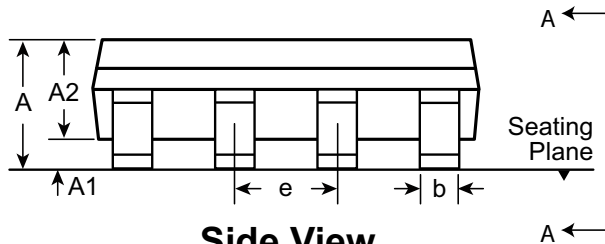
4.90x3.90mm body, 1.75mm height (max), 1.27mm pitch



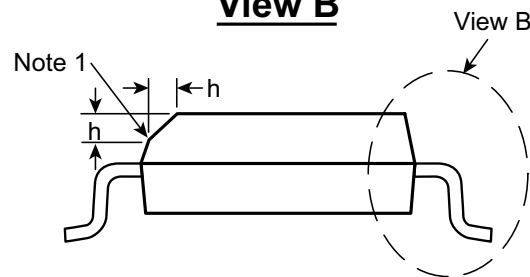
**Top View**



**View B**



**Side View**



**View A-A**

**Note:**  
 1. This chamfer feature is optional. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

Symbol	A	A1	A2	b	D	E	E1	e	h	L	L1	L2	θ	θ1	
Dimension (mm)	MIN	1.35*	0.10	1.25	0.31	4.80*	5.80*	3.80*	1.27 BSC	0.25	0.40	1.04 REF	0.25 BSC	0°	5°
	NOM	-	-	-	-	4.90	6.00	3.90		-	-			-	-
	MAX	1.75	0.25	1.65*	0.51	5.00*	6.20*	4.00*		0.50	1.27			8°	15°

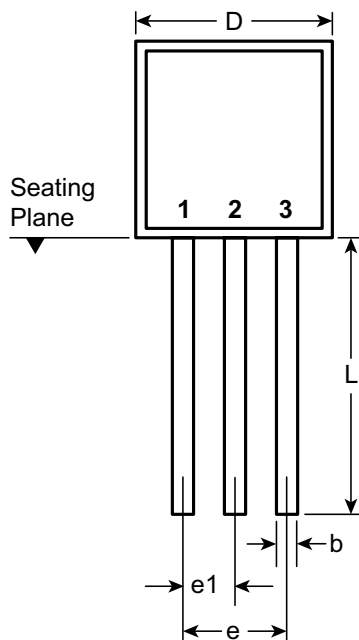
JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.

\* This dimension is not specified in the JEDEC drawing.

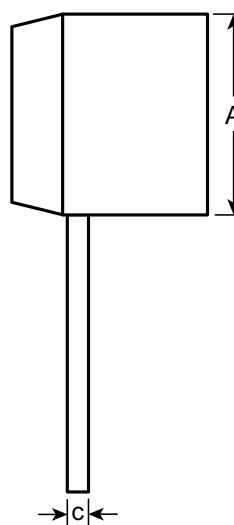
Drawings are not to scale.

Supertex Doc. #: DSPD-8SOLGTG, Version I041309.

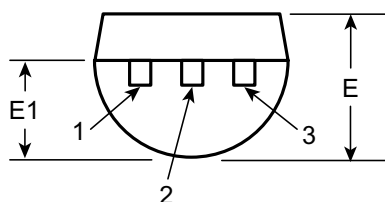
### 3-Lead TO-92 Package Outline (N3)



**Front View**



**Side View**



**Bottom View**

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

\* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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